

ROITHNER LASERTECHNIK

**A-1040 WIEN, FLEISCHMANNGASSE 9
TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43
e-mail: rlt@mcb.at http://www.roithner.mcb.at**

RLT6505MG TECHNICAL DATA



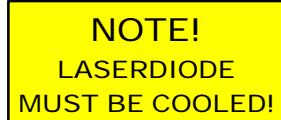
Visible Wavelength Laserdiode

Structure: AlGaInP, index guided, single transverse mode

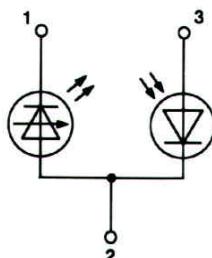
Lasing wavelength: 650 nm

Max. optical power: 5 mW

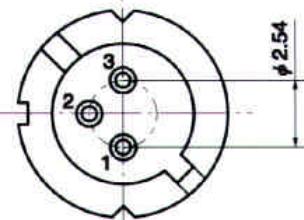
Package: 5.6 mm



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (Tc=25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|----------------------------|--------------------|------------|------|
| Optical Output Power | P _o | 5 | mW |
| LD Reverse Voltage | V _{R(LD)} | 2 | V |
| PD Reverse Voltage | V _{R(PD)} | 30 | V |
| Operation Case Temperature | T _C | -10 .. +40 | °C |
| Storage Temperature | T _{STG} | -40 .. +85 | °C |

Optical-Electrical Characteristics (Tc = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN | TYP | MAX | UNIT |
|----------------------|-----------------|--|-----|-----|-----|------|
| Optical Output Power | P _o | kink free | | | 5 | mW |
| Threshold Current | I _{th} | cw | 20 | 30 | 40 | mA |
| Operation Current | I _{op} | P _o = 5 mW | | 45 | 70 | mA |
| Operating Voltage | V _{op} | P _o = 5 mW | | 2.2 | 2.7 | V |
| Lasing Wavelength | λ _p | P _o = 5 mW | | 650 | 655 | nm |
| Beam Divergence | θ | P _o = 5 mW | 5 | 8 | 11 | ° |
| Beam Divergence | θ _⊥ | P _o = 5 mW | 25 | 31 | 37 | ° |
| Astigmatism | A _s | P _o = 5 mW, NA = 0.4 | | 11 | | μm |
| Monitor Current | I _m | P _o = 5 mW, V _r = 5V | | 10 | 200 | μA |